

11th International "Hiroshima" Symposium on the Development and Application of Semiconductor Tracking Detectors (HSTD11) in conjunction with 2nd Workshop on SOI Pixel Detectors (SOIPIX2017) at OIST, Okinawa, Japan

Contribution ID: 15

Type: ORAL

High Resolution SOI Pixel Detector

Monday, 11 December 2017 15:20 (30 minutes)

Silicon-On-Insulator (SOI) technology is considered to have the most suitable structure for a monolithic pixel detector. It achieved many important performance: less than 1 micron tracking resolution, good energy resolution with 10 electron noise level, radiation hardness of more than 100 kGy(Si), small layout size with PMOS and NMOS active merge, etc.

Overview of the SOI pixel process and detector development will be presented.

Primary author: Prof. ARAI, Yasuo (High Energy Accelerator Research Organization (JP))

Presenter: Prof. ARAI, Yasuo (High Energy Accelerator Research Organization (JP))

Session Classification: Session3

Track Classification: SOI detectors